

Zakhar D Kovalyuk

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

212
papers

3,184
citations

22
h-index

51
g-index

226
ext. papers

3,747
ext. citations

2.8
avg, IF

4.88
L-index

#	Paper	IF	Citations
212	Terahertz control of photoluminescence emission in few-layer InSe. <i>Applied Physics Letters</i> , 2022 , 120, 092104	3.4	0
211	Large Tunneling Magnetoresistance in van der Waals Ferromagnet/Semiconductor Heterojunctions. <i>Advanced Materials</i> , 2021 , e2104658	24	10
210	Charge Carrier Transport in Van Der Waals Semiconductor InSe Intercalated with RbNO ₃ Probed by Direct Current Methods. <i>Applied Sciences (Switzerland)</i> , 2021 , 11, 5181	2.6	
209	Anomalous Low Thermal Conductivity of Atomically Thin InSe Probed by Scanning Thermal Microscopy. <i>Advanced Functional Materials</i> , 2021 , 31, 2008967	15.6	4
208	Ferroelectric semiconductor junctions based on graphene/In ₂ Se ₃ /graphene van der Waals heterostructures. <i>2D Materials</i> , 2021 , 8, 045020	5.9	4
207	Tunable spin-orbit coupling in two-dimensional InSe. <i>Physical Review B</i> , 2021 , 104,	3.3	2
206	Resonance and antiresonance in Raman scattering in GaSe and InSe crystals. <i>Scientific Reports</i> , 2021 , 11, 924	4.9	2
205	Enhanced Optical Emission from 2D InSe Bent onto Si-Pillars. <i>Advanced Optical Materials</i> , 2020 , 8, 2000888	8.8	10
204	The Interaction of Hydrogen with the van der Waals Crystal -InSe. <i>Molecules</i> , 2020 , 25,	4.8	8
203	Interlayer Band-to-Band Tunneling and Negative Differential Resistance in van der Waals BP/InSe Field-Effect Transistors. <i>Advanced Functional Materials</i> , 2020 , 30, 1910713	15.6	41
202	Resonant tunnelling into the two-dimensional subbands of InSe layers. <i>Communications Physics</i> , 2020 , 3,	5.4	13
201	Formation of PbMnI ₂ alloys: Structural, photoluminescence and nuclear quadrupole resonance studies. <i>Journal of Alloys and Compounds</i> , 2020 , 824, 153985	5.7	1
200	Design of van der Waals interfaces for broad-spectrum optoelectronics. <i>Nature Materials</i> , 2020 , 19, 299-304	30.4	64
199	Photoluminescence dynamics in few-layer InSe. <i>Physical Review Materials</i> , 2020 , 4,	3.2	7
198	Van der Waals SnSe ₂ (1-x)S _{2x} Alloys: Composition-Dependent Bowing Coefficient and Electron-Phonon Interaction. <i>Advanced Functional Materials</i> , 2020 , 30, 1908092	15.6	10
197	High-Frequency Elastic Coupling at the Interface of van der Waals Nanolayers Imaged by Picosecond Ultrasonics. <i>ACS Nano</i> , 2019 , 13, 11530-11537	16.7	15
196	Formation and Healing of Defects in Atomically Thin GaSe and InSe. <i>ACS Nano</i> , 2019 , 13, 5112-5123	16.7	23

195	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. <i>Nano Letters</i> , 2019 , 19, 6475-6481	11.5	26
194	Schottky-barrier thin-film transistors based on HfO ₂ -capped InSe. <i>Applied Physics Letters</i> , 2019 , 115, 033502	3.4	10
193	Photoquantum Hall Effect and Light-Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. <i>Advanced Functional Materials</i> , 2019 , 29, 1805491	15.6	13
192	Improved performance of InSe field-effect transistors by channel encapsulation. <i>Semiconductor Science and Technology</i> , 2018 , 33, 06LT01	1.8	11
191	Coherent acoustic phonons in van der Waals nanolayers and heterostructures. <i>Physical Review B</i> , 2018 , 98,	3.3	19
190	Magnetotransport and lateral confinement in an InSe van der Waals Heterostructure. <i>2D Materials</i> , 2018 , 5, 035040	5.9	6
189	Effect of the electron irradiation on electrical properties of n-InSe and their anisotropy. <i>Nuclear Physics and Atomic Energy</i> , 2018 , 19, 136-144	0.3	1
188	Features of magnetoresistance and magnetic properties in Bi _{95.69} Mn _{3.69} Fe _{0.62} . <i>Low Temperature Physics</i> , 2018 , 44, 1153-1160	0.7	
187	Impedance and Photosensitivity Spectra of Nanocomposite Structures Based on Layered Semiconductor InSe and Ionic Salt RbNO ₃ . <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018 , 215, 1800460	1.6	1
186	Epitaxial growth of InSe and In ₂ Se ₃ on GaSe. <i>2D Materials</i> , 2018 , 5, 035026	5.9	55
185	Gate-Defined Quantum Confinement in InSe-Based van der Waals Heterostructures. <i>Nano Letters</i> , 2018 , 18, 3950-3955	11.5	33
184	Room Temperature Uniaxial Magnetic Anisotropy Induced By Fe-Islands in the InSe Semiconductor Van Der Waals Crystal. <i>Advanced Science</i> , 2018 , 5, 1800257	13.6	5
183	Engineering p-n junctions and bandgap tuning of InSe nanolayers by controlled oxidation. <i>2D Materials</i> , 2017 , 4, 025043	5.9	63
182	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. <i>Physical Review Letters</i> , 2017 , 119, 157701	7.4	33
181	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. <i>Nature Nanotechnology</i> , 2017 , 12, 223-227	28.7	723
180	Effect of Electron Irradiation on Conductivity Anisotropy in n-InSe. <i>Journal of Nano- and Electronic Physics</i> , 2017 , 9, 06013-1-06013-5	1.5	2
179	Excitonic photoconductivity of heterostructures based on gallium and indium selenides. <i>Functional Materials</i> , 2017 , 24, 005-205	0.6	
178	Observation of an inductive-like effect in a supercapacitor. <i>Technical Physics Letters</i> , 2016 , 42, 325-327	0.7	

177	Nanomechanical probing of the layer/substrate interface of an exfoliated InSe sheet on sapphire. <i>Scientific Reports</i> , 2016 , 6, 26970	4.9	13
176	Preparation of Nanocomposite Magnetic Compounds Based on Layered Semiconductors by Means of Electrochemical Intercalation in a Gradient Magnetic Field. <i>Acta Physica Polonica A</i> , 2016 , 130, 773-777	0.6	0
175	Physical properties of layered FeIn ₂ Se ₄ single crystals. <i>Functional Materials</i> , 2016 , 23, 557-560	0.6	
174	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. <i>Scientific Reports</i> , 2016 , 6, 39619	4.9	114
173	Highly-mismatched InAs/InSe heterojunction diodes. <i>Applied Physics Letters</i> , 2016 , 109, 182115	3.4	9
172	Quantum confinement and photoresponsivity of In ₂ Se ₃ nanosheets grown by physical vapour transport. <i>2D Materials</i> , 2016 , 3, 025030	5.9	68
171	Electrical and Photoelectric Properties of the TiN/p-InSe Heterojunction. <i>Semiconductors</i> , 2016 , 50, 334-338	3.3	4
170	Prompt quality monitoring of InSe and GaSe semiconductor crystals by the nuclear quadrupole resonance technique. <i>Semiconductors</i> , 2016 , 50, 1034-1037	0.7	4
169	Biexciton formation and exciton coherent coupling in layered GaSe. <i>Journal of Chemical Physics</i> , 2015 , 142, 212422	3.9	24
168	Photoelectric properties of n-ITO/p-GaTe heterojunctions. <i>Semiconductors</i> , 2015 , 49, 600-603	0.7	1
167	Graphene-InSe-graphene van der Waals heterostructures. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012001	0.3	9
166	Electrochemical, optical, and magnetic properties of Ni _x GaSe (0 Inorganic Materials, 2015 , 51, 1086-1089)	0.9	0
165	Graphitic carbon/n-CdTe Schottky-type heterojunction solar cells prepared by electron-beam evaporation. <i>Solar Energy</i> , 2015 , 112, 78-84	6.8	17
164	Two-band conduction in electron-irradiated n-InSe single crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2015 , 252, 346-356	1.3	3
163	Nanocomposite structures grown by inserting ionic salt RbNO ₃ into van der Waals gaps of III-VI compound layered semiconductors. <i>Solid State Ionics</i> , 2015 , 273, 59-65	3.3	4
162	High broad-band photoresponsivity of mechanically formed InSe-graphene van der Waals heterostructures. <i>Advanced Materials</i> , 2015 , 27, 3760-6	24	252
161	Fabrication and characterization of PbSe nanostructures on van der Waals surfaces of GaSe layered semiconductor crystals. <i>Nanotechnology</i> , 2015 , 26, 465601	3.4	3
160	Anisotropy of resistivity in Bi _{93.99} Mn ₆ Fe _{0.01} . <i>Low Temperature Physics</i> , 2015 , 41, 314-316	0.7	1

159	Temperature dependent electrical properties and barrier parameters of photosensitive heterojunctions n-Tl/p-Cd _{1-x} Zn _x Te. <i>Semiconductor Science and Technology</i> , 2015 , 30, 075006	1.8	8
158	2D nanocomposite photoconductive sensors fully dry drawn on regular paper. <i>Nanotechnology</i> , 2015 , 26, 255501	3.4	12
157	Structural characteristics and magnetic properties of cobalt-intercalated A ₅₂ B ₆₃ single crystals. <i>Technical Physics</i> , 2015 , 60, 1658-1662	0.5	1
156	Morphology of Van der Waals surfaces and magnetic hysteresis in cobalt intercalated InTe. <i>Functional Materials</i> , 2015 , 22, 327-331	0.6	
155	Structure of oxidized and unoxidized end faces of GaSe layered crystals. <i>Inorganic Materials</i> , 2014 , 50, 339-343	0.9	6
154	Effect of bremsstrahlung γ photons and neutrons on the parameters of indium-selenium photoconverters. <i>Semiconductors</i> , 2014 , 48, 239-244	0.7	3
153	Mechanism of excitonic dephasing in layered InSe crystals. <i>Physical Review B</i> , 2014 , 89,	3.3	22
152	Spectral anisotropy of a photoresponse from heterojunctions based on GaSe and InSe layered crystals. <i>Technical Physics</i> , 2014 , 59, 407-410	0.5	4
151	Structure and magnetic properties of cobalt-intercalated layered InSe crystals. <i>Technical Physics</i> , 2014 , 59, 1462-1465	0.5	2
150	Electrochemical, optical, and magnetic properties of Ni _x InSe (0 Inorganic Materials, 2014 , 50, 976-980	0.9	2
149	Photosensitive anisotype n-ZnSe/p-InSe and n-ZnSe/p-GaSe heterojunctions. <i>Technical Physics</i> , 2014 , 59, 1205-1208	0.5	5
148	Influence of Optical Illumination on the Electric Impedance of Composite Nanostructures Based on p-GaSe Layered Semiconductor with 3D Nanodimensional Inclusions of KNO ₃ Ferroelectric. <i>Russian Physics Journal</i> , 2014 , 57, 642-656	0.7	
147	Effect of low-temperature annealing on the quality of InSe layered single crystals and the characteristics of n-InSe/p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 545-550	0.7	6
146	On the photopleochroism coefficient and its temperature dynamics in native oxide-p-InSe heterojunctions. <i>Semiconductors</i> , 2014 , 48, 776-778	0.7	3
145	Morphology, chemical composition, and electrical characteristics of hybrid (Ni-C) nanocomposite structures grown on the van der Waals GaSe(0001) surface. <i>Physics of the Solid State</i> , 2014 , 56, 2118-2130	0.8	2
144	Room Temperature Electroluminescence from Mechanically Formed van der Waals III-VI Homojunctions and Heterojunctions. <i>Advanced Optical Materials</i> , 2014 , 2, 1064-1069	8.1	61
143	Quantum confined acceptors and donors in InSe nanosheets. <i>Applied Physics Letters</i> , 2014 , 105, 221909	3.4	53
142	Magnetic properties and surface morphology of layered In ₂ Se ₃ crystals intercalated with cobalt. <i>Physics of the Solid State</i> , 2013 , 55, 1148-1155	0.8	14

141	Tuning the bandgap of exfoliated InSe nanosheets by quantum confinement. <i>Advanced Materials</i> , 2013 , 25, 5714-8	24	419
140	Electrical properties of an n-TiO ₂ /n-GaP semiconductor heterostructure. <i>Russian Physics Journal</i> , 2013 , 56, 233-235	0.7	
139	Temperature and baric dependence of nuclear quadruple resonance spectra in indium and gallium monoselenides 2013 ,		3
138	Sensitive elements of pressure transducers made of layered intercalated InSe, GaSe, and Bi ₂ Te ₃ crystals. <i>Technical Physics</i> , 2013 , 58, 1840-1843	0.5	2
137	SurfaceBarrier heterojunctions TiO ₂ /CdZnTe. <i>Semiconductor Science and Technology</i> , 2013 , 28, 015014	1.8	8
136	Electrical and optical properties of Al ³⁺ -intercalated InSe and GaSe. <i>Inorganic Materials</i> , 2013 , 49, 22-27	0.9	2
135	Influence of external factors on the self-organization of lead and tin telluride nanostructures on the BaF ₂ (111) surface under conditions close to the thermodynamic equilibrium. <i>Physics of the Solid State</i> , 2013 , 55, 181-195	0.8	5
134	Fabrication and Characterization of Photosensitive n-CdO/p-InSe Heterojunctions. <i>Acta Physica Polonica A</i> , 2013 , 124, 720-723	0.6	6
133	Preparation and properties of electrets based on iodine-intercalated InSe and GaSe. <i>Inorganic Materials</i> , 2012 , 48, 776-780	0.9	
132	Optical properties of TiO ₂ -MnO ₂ thin films prepared by electron-beam evaporation. <i>Technical Physics</i> , 2012 , 57, 1148-1151	0.5	17
131	Electrical properties of anisotype heterojunctions n-CdZnO/p-CdTe. <i>Semiconductors</i> , 2012 , 46, 1152-1157	0.7	15
130	Ferromagnetism of layered GaSe semiconductors intercalated with cobalt. <i>Semiconductors</i> , 2012 , 46, 971-974	0.7	12
129	Optical constants and polarimetric properties of ZnMnO ₂ thin films. <i>Optical Materials</i> , 2012 , 34, 1940-1945	1.3	18
128	Effect of annealing on the spectra of nuclear quadrupole resonance in gallium-indium selenides and characteristics of structures based on these materials. <i>Semiconductors</i> , 2012 , 46, 1145-1151	0.7	2
127	On the Possibility of Layered Crystals Application for Solid State Hydrogen Storages - InSe and GaSe Crystals 2012 ,		6
126	Light-dependent IV characteristics of TiO ₂ /CdTe heterojunction solar cells. <i>Semiconductor Science and Technology</i> , 2012 , 27, 055008	1.8	20
125	Electrical properties of In ₂ Se ₃ <Mn> and InSe<Mn> crystals. <i>Inorganic Materials</i> , 2012 , 48, 103-105	0.9	4
124	Diffraction properties of the nanostructured surface. <i>Journal of Nanoscience and Nanotechnology</i> , 2012 , 12, 8856-9	1.3	

123	Investigation of InS-InSe heterojunctions prepared using sulphurization of p-InSe. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2012 , 15, 38-40	0.4	
122	NMR Investigations of Hydrogen Intercalates in GaSe Layered Crystals. <i>NATO Science for Peace and Security Series C: Environmental Security</i> , 2011 , 443-458	0.3	1
121	Electrical and photoelectrical properties of photosensitive heterojunctions n-TiO ₂ /p-CdTe. <i>Semiconductor Science and Technology</i> , 2011 , 26, 125006	1.8	39
120	Surface morphology and electrical resistance of the oxide film on InSe. <i>Inorganic Materials</i> , 2011 , 47, 749-752	0.9	5
119	Negative capacitance of native oxide films on (0001) InSe fracture surfaces. <i>Inorganic Materials</i> , 2011 , 47, 847-852	0.9	2
118	Asymmetric current flow in a native oxide/indium selenide heterostructure. <i>Inorganic Materials</i> , 2011 , 47, 1178-1182	0.9	2
117	Crystal growth and elastic properties of In ₂ Se ₃ . <i>Inorganic Materials</i> , 2011 , 47, 1174-1177	0.9	7
116	Carrier transport in layered semiconductor (p-GaSe)-ferroelectric (KNO ₃) composite nanostructures. <i>Semiconductors</i> , 2011 , 45, 338-349	0.7	6
115	Mechanisms of charge transport in anisotype n-TiO ₂ /p-CdTe heterojunctions. <i>Semiconductors</i> , 2011 , 45, 1077-1081	0.7	28
114	The electric field gradient asymmetry parameter in InSe. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2011 , 14, 164-166	0.4	1
113	Surface structure of unoxidized and oxidized Bi ₂ Se ₃ crystals. <i>Inorganic Materials</i> , 2010 , 46, 1296-1298	0.9	6
112	Electrical properties of hybrid (ferromagnetic metal)(layered semiconductor) Ni/pGaSe structures. <i>Semiconductors</i> , 2010 , 44, 171-183	0.7	7
111	Electrical properties of magnesium-intercalated InSe. <i>Inorganic Materials</i> , 2009 , 45, 846-850	0.9	2
110	Optical and photoelectric properties of barium-intercalated InSe and GaSe. <i>Inorganic Materials</i> , 2009 , 45, 1222-1225	0.9	7
109	Radiation resistance of photodiodes based on indium monoselenides under β radiation. <i>Journal of Nuclear Materials</i> , 2009 , 385, 489-494	3.3	4
108	Current instability with Z- and N-shaped current-voltage characteristics in inhomogeneous In ₂ Se ₃ crystals. <i>Technical Physics Letters</i> , 2009 , 35, 569-572	0.7	0
107	Neutron diffraction studies of the negative thermal expansion in a layered indium selenide crystal. <i>Physics of the Solid State</i> , 2009 , 51, 2342-2346	0.8	4
106	Electric performance and photosensitivity of heterostructures prepared by thermal decomposition of a gallium nitrate aqueous solution on an indium selenide (0001) cleaved surface. <i>Technical Physics</i> , 2009 , 54, 397-401	0.5	1

105	An innovative and viable route for the realization of ultra-thin supercapacitors electrodes assembled with carbon nanotubes. <i>Journal of Nanoscience and Nanotechnology</i> , 2009 , 9, 2124-7	1.3	1
104	Fine structure of NQR spectra in GaSe. <i>Semiconductor Physics, Quantum Electronics and Optoelectronics</i> , 2009 , 12, 370-374	0.4	1
103	Hydrogen Sorption in Layered Nanoporous GaSe Crystals. <i>NATO Science for Peace and Security Series C: Environmental Security</i> , 2008 , 765-777	0.3	2
102	Oxide films on the surface of GaSe doped with Cd or Dy. <i>Inorganic Materials</i> , 2008 , 44, 680-686	0.9	1
101	Age-induced oxide on cleaved surface of layered GaSe single crystals. <i>Applied Surface Science</i> , 2008 , 254, 2067-2071	6.7	7
100	The formation of organic (propolis films)/inorganic (layered crystals) interfaces for optoelectronic applications. <i>Superlattices and Microstructures</i> , 2008 , 44, 563-570	2.8	9
99	Surface topology of GaSe oxidized crystals. <i>Superlattices and Microstructures</i> , 2008 , 44, 416-419	2.8	13
98	Native oxide emerging of the cleavage surface of gallium selenide due to prolonged storage. <i>Semiconductors</i> , 2008 , 42, 414-421	0.7	21
97	Electrical and photoelectric characteristics of structures based on InSe and GaSe layered semiconductors irradiated with 12.5-MeV electrons. <i>Semiconductors</i> , 2008 , 42, 1292-1297	0.7	7
96	X-ray diffraction study of the molecular propolis films deposited from an alcohol solution onto the cleavage surfaces of layered V2VI3 compounds. <i>Technical Physics</i> , 2008 , 53, 1215-1221	0.5	3
95	Ferromagnetism of Narrow-Gap $\text{Ge}_{1-x}\text{ySn}_x\text{MnyTe}$ and Layered $\text{In}_{1-x}\text{MnxSe}$ Semiconductors. <i>Acta Physica Polonica A</i> , 2008 , 114, 1219-1227	0.6	3
94	Electrical, luminescent and photovoltaic properties of the indium tin oxide/GaSe heterojunctions with a thin layer of gallium oxide. <i>Thin Solid Films</i> , 2007 , 515, 6356-6359	2.2	3
93	Anomalies of magnetic properties of layered crystals InSe containing Mn. <i>Materials Science and Engineering C</i> , 2007 , 27, 1052-1055	8.3	13
92	Electrical properties of In_2Se_3 layered crystals doped with cadmium, iodine, or copper. <i>Inorganic Materials</i> , 2007 , 43, 1271-1274	0.9	11
91	Effect of the buffer layer of GaSe intrinsic oxide with nanometer thickness on electrical, photoelectric, and emissive properties of ITO-GaSe heterostructures. <i>Semiconductors</i> , 2007 , 41, 301-306	0.7	5
90	The effect of neutron radiation on the photoelectric parameters of ITO-GaSe structures. <i>Semiconductors</i> , 2007 , 41, 550-554	0.7	5
89	A study of isotype photosensitive heterostructures (intrinsic oxide)-n-InSe prepared by long-term thermal oxidation. <i>Semiconductors</i> , 2007 , 41, 1056-1059	0.7	3
88	Experimental investigation of effect of aromatic hydrocarbons on resistivity of indium selenide. <i>Semiconductors</i> , 2007 , 41, 1197-1200	0.7	3

87	Formation of nanostructure on the surface of layered InSe semiconductor caused by oxidation under heating. <i>Physics of the Solid State</i> , 2007 , 49, 1572-1578	0.8	22
86	Photosensitivity of heterojunctions formed by deposition of gum on a layered III-VI semiconductor. <i>Technical Physics</i> , 2007 , 52, 1178-1182	0.5	2
85	Self-organization of PbTe and SnTe nanostructures on the van der Waals GaSe(0001) surface. <i>Technical Physics Letters</i> , 2007 , 33, 86-90	0.7	15
84	Effect of neutron radiation on the photoelectric parameters of p-n-InSe structures. <i>Technical Physics Letters</i> , 2007 , 33, 767-770	0.7	5
83	APPLICATION OF LAYERED InSe AND GaSe CRYSTALS AND POWDERS FOR SOLID STATE HYDROGEN STORAGE 2007 , 325-340		9
82	Structural and optical characterization of the propolis films. <i>Applied Surface Science</i> , 2006 , 253, 279-282	6.7	8
81	Electrical properties of hydrogenated InSe crystals. <i>Inorganic Materials</i> , 2006 , 42, 1308-1310	0.9	2
80	Change of built-in-potential in heterostructures induced by X-ray irradiation. <i>Nuclear Instruments & Methods in Physics Research B</i> , 2006 , 246, 118-121	1.2	2
79	Mechanisms of current transfer and photosensitivity in Zn/CuInSe ₂ Schottky diodes. <i>Technical Physics Letters</i> , 2006 , 32, 459-462	0.7	2
78	Characteristics of the oxide-p-InSe heterojunctions exposed to irradiation with X-ray photons. <i>Semiconductors</i> , 2006 , 40, 911-914	0.7	3
77	X-ray diffraction investigation of the structure of propolis films. <i>Physics of the Solid State</i> , 2006 , 48, 1602-1604	16.04	2
76	Photovoltaic Effect in the Anisotype GaSe-InSe Heterojunctions Under Pressure. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 865, 511		1
75	Ferromagnetic states in the In _{1-x} Mn _x Se layered crystal. <i>Physical Review B</i> , 2005 , 71,	3.3	13
74	Gamma radiation influence on the photoelectrical properties of oxide-p-InSe heterostructure. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2005 , 118, 147-149	3.1	6
73	Effect of uniaxial compression on the photoconversion parameters in a p-GaSe-n-InSe optical contact. <i>Semiconductors</i> , 2005 , 39, 600-602	0.7	3
72	Effect of gamma radiation on the properties of InSe photodiodes. <i>Technical Physics Letters</i> , 2005 , 31, 359-360	0.7	13
71	Optical and electrical properties of turpentine films. <i>Technical Physics</i> , 2005 , 50, 787-789	0.5	1
70	Weak ferromagnetism in InSe:Mn layered crystals. <i>Semiconductors</i> , 2005 , 39, 772-776	0.7	7

69	Asymmetric current transfer in isotype n-In ₂ Se ₃ /n-InSe heterocontacts. <i>Technical Physics Letters</i> , 2005 , 31, 728	0.7	2
68	A heterocontact in the semiconductor-mumie system. <i>Technical Physics Letters</i> , 2005 , 31, 772	0.7	
67	Properties of Hydrogenated GaSe Crystals. <i>Inorganic Materials</i> , 2005 , 41, 793-795	0.9	9
66	Spectroscopic studies of 2H-PbI ₂ (Mn) layered crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2005 , 242, 2427-2432	1.3	6
65	The Influence of Hydrogen on the Electrical and Photoelectric Properties of Photodiodes Based on Indium Monoselenide. <i>Materials Research Society Symposia Proceedings</i> , 2005 , 884, 1		
64	Optical Investigation of Hydrogen Intercalation-Deintercalation Processes in Layered Semiconductor-InSe Crystals. <i>NATO Science Series Series II, Mathematics, Physics and Chemistry</i> , 2004 , 519-530		1
63	Photosensitivity of the semiconductor-turpentine heterocontact. <i>Technical Physics Letters</i> , 2004 , 30, 250-252	0.7	1
62	Oxide-p-InSe heterostructures with improved photoelectric characteristics. <i>Semiconductors</i> , 2004 , 38, 402-405	0.7	5
61	Variation in the built-in potential of a photodiode based on an n-InSe-p-GaSe heterojunction in the course of aging. <i>Semiconductors</i> , 2004 , 38, 546-549	0.7	8
60	On the mechanism of current passage in metal/p-CuInSe ₂ structures. <i>Technical Physics</i> , 2004 , 49, 658-659	0.5	1
59	Surface barrier Sn-CuInSe ₂ junctions. <i>Technical Physics Letters</i> , 2004 , 30, 402-403	0.7	2
58	Optical and electrical properties of propolis films. <i>Technical Physics</i> , 2004 , 49, 1529-1530	0.5	3
57	Intrinsic conductive oxide-p-InSe solar cells. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2004 , 109, 252-255	3.1	26
56	Anomalies in static and dynamic conductivity of indium monoselenide. <i>Semiconductors</i> , 2003 , 37, 134-135	0.7	1
55	Electrical properties of the p ⁺ -Bi ₂ Te ₃ -p-GaSe isotype heterostructure. <i>Semiconductors</i> , 2003 , 37, 172-173	0.7	1
54	Barrier formation in a heterostructure formed of native oxide and p-InSe. Electrical and photoelectrical properties. <i>Semiconductors</i> , 2003 , 37, 187-193	0.7	2
53	Energy band diagram of a photosensitive Sn-p-InSe structure. <i>Technical Physics Letters</i> , 2003 , 29, 480-481	0.7	5
52	Semiconductor-propolis heterojunction. <i>Technical Physics Letters</i> , 2003 , 29, 867-870	0.7	2

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